Form PTO-1449	ATTORNEY DOCKET NO. 10003976-4	SERIAL NO. TBA
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT Moll *et al.*	
(Use several sheets if necessary)	FILING DATE TBA	GROUP TBA

REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL	*	DOCUMENT NUMBER	DATE	NAME
DF	AA.	6,388,307	05/14/02	Kondo et al.
	AB	2002/0027232 A1	03/07/02	Shigematsu et al.
	AC	6,339,233	01/15/02	Lell
	AD	6,316,795	11/13/01	Croke, III
	AE	6,251,738	06/26/01	Huang
	AF	5,387,808	02/07/95	Nozu
	AG	5,349,201	09/20/94	Stanchina et al.
DF	AH	4,821,082	04/11/89	Frank et al.

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	TRANSLATION YES	TRANSLATION NO
DF	BA	EPO-0571994A2	05/27/93	Stanchina, William E.	X	
	BB	JP-6-224230	08/12/94	Yashiki et al.		X
DF	BC	WO 01/09957 A1	02/08/01	Micovic, Miroslav	X	

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

DF	CA	Bell Telephone Laboratories, Inc., **Semiconductor Device, Physics and Technology**, *S.M. SZE, AT&T Bell Laboratories, 1985,* (267-269)
	CB	G.J. Sullivan, *et al.*, **MBE Growth and Characterization of High Gain AlGaAs/GaAsSb/GaAs NpN HBTs,** *Inst. Phys. Conf. Ser. No.120: Chapter 13, 1991 (647-650)*
	CC	N. Matine, *et al.*, **Electrical Stress Damage Reversed in Non-Passivated Fully Self-Aligned InP HBTs By Ozone Surface Treatment,** *Electronics Letters, December 9, 1999,* Vol. 35, No. 25
	CD	C.R. Bolognesi, *et al.*, **High Performance InP/GaAsSb/InP DHBT s With Heavily Doped Base Layers,** *2000 IEEE, (12-18)*
	CE	S.P. Watkins, *et al.*, **Heavily Carbon-Doped GaAsSb Grown on InP For HBT Applications,** *Journal of Crystal Growth 221 (2000)* (59-65)
	CF	M.W. Dvorak, *et al.* **Abrupt Junction InP/GaAsSb/InP Double Heterojunction Bipolar Transistors With F_t as High As 250 GH_z and BV $_{CEO}$ > 6V,** *2000 IEEE* (178-181)
	CG	Tohru Oka, *et al.* **Low Turn-on Voltage GaAs Heterojunction Bipolar Transistors With a Pseudomorphic GaAsSb Base,** *Applied Physics Letters,* Vol 78, No. 4, 2001, (483485)
DF	CH	M.W. Dvorak, *et al.*, **MOCVD-Grown 175 GHz InP/GaAs$_x$Sb$_{1-x}$/InP DHBTs With High Current Gains Using Strained and Heavily C-Doped Base Layers**

EXAMINER [signature] DATE CONSIDERED 5/16/06

* Copies of these references are not enclosed Pursuant to 37 CFR 1.98(d). (See accompanying IDS)